

IN THE CLAIMS:

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~striketrough~~. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered).

Please AMEND claim 1 and ADD new claim 4 in accordance with the following:

1. (CURRENTLY AMENDED) A power semiconductor module, comprising:
a metal base comprising a heat sink;
a semiconductor chip;
a ceramic substrate;
a circuit assembly body comprising a ceramic plate, an upper circuit plate, and the ceramic substrate, wherein the semiconductor chip is placed on the ceramic substrate which is then placed on the metal base; and
an outer case joined to the metal base and having terminals formed integrally therein, wherein a casting method integrally molds the metal base on the underside of the ceramic plate of the ceramic substrate, which has no lower plate [.] and in which the upper circuit plate is joined to the ceramic plate.
2. (ORIGINAL) The power semiconductor module according to claim 1, wherein the power semiconductor module comprises placing at least one ceramic substrate on the metal base.
3. (ORIGINAL) A power semiconductor module, comprising:
a metal base comprising a heat sink;
a semiconductor chip;
a ceramic substrate;
a circuit assembly body comprising the ceramic substrate, wherein the semiconductor chip is placed on the ceramic substrate which is then placed on the metal base; and
an outer case having terminals formed integrally therein,
wherein an upper circuit plate and the metal base are formed directly by a formation of a layer of molten metal on an upper face and a lower face of the ceramic plate, respectively.

4. (NEW) A method of forming a power semiconductor module, comprising:
placing a semiconductor chip on a ceramic substrate;
placing the ceramic substrate on a metal base comprising a heat sink; and
forming a layer of molten metal on an upper face and a lower face of the ceramic substrate to directly form an upper circuit plate and the metal base.